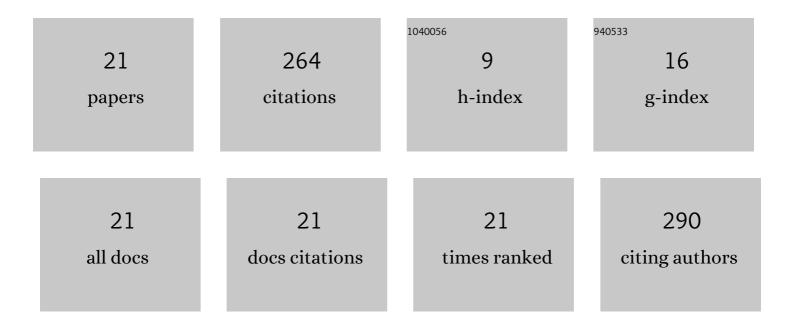
Youngin Jeon

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Top-Down Fabrication of Fully CMOS-Compatible Silicon Nanowire Arrays and Their Integration into CMOS Inverters on Plastic. ACS Nano, 2011, 5, 2629-2636.	14.6	57
2	Steep Subthreshold Swing n- and p-Channel Operation of Bendable Feedback Field-Effect Transistors with p ⁺ –i–n ⁺ Nanowires by Dual-Top-Gate Voltage Modulation. Nano Letters, 2015, 15, 4905-4913.	9.1	47
3	Switching Characteristics of Nanowire Feedback Field-Effect Transistors with Nanocrystal Charge Spacers on Plastic Substrates. ACS Nano, 2014, 8, 3781-3787.	14.6	28
4	Light-emitting diodes composed of n-ZnO and p-Si nanowires constructed on plastic substrates by dielectrophoresis. Solid State Sciences, 2011, 13, 1735-1739.	3.2	21
5	Impact-Ionization and Tunneling FET Characteristics of Dual-Functional Devices With Partially Covered Intrinsic Regions. IEEE Nanotechnology Magazine, 2015, 14, 633-637.	2.0	15
6	NOR logic function of a bendable combination of tunneling field-effect transistors with silicon nanowire channels. Nano Research, 2016, 9, 499-506.	10.4	12
7	Comparative performance analysis of silicon nanowire tunnel FETs and MOSFETs on plastic substrates in flexible logic circuit applications. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1350-1358.	1.8	11
8	Flexible semi-around gate silicon nanowire tunnel transistors with a sub-kT/q switch. Journal of Applied Physics, 2015, 117, 224502.	2.5	11
9	Si-Based Flexible Memristive Systems Constructed Using Top-Down Methods. ACS Applied Materials & Interfaces, 2011, 3, 3957-3961.	8.0	10
10	Flexible Nano-Floating-Gate Memory With Channels of Enhancement-Mode Si Nanowires. IEEE Transactions on Electron Devices, 2012, 59, 2939-2942.	3.0	10
11	Flexible Logic Gates Composed of Si-Nanowire-Based Memristive Switches. IEEE Transactions on Electron Devices, 2012, 59, 3288-3291.	3.0	9
12	Enhancement of Trap-Assisted Green Electroluminescence Efficiency in ZnO/SiO ₂ /Si Nanowire Light-Emitting Diodes on Bendable Substrates by Piezophototronic Effect. ACS Applied Materials & Interfaces, 2016, 8, 2764-2773.	8.0	9
13	Strain-Dependent Characteristics of Triangular Silicon Nanowire-Based Field-Effect Transistors on Flexible Plastics. Japanese Journal of Applied Physics, 2011, 50, 065001.	1.5	5
14	Flexible silicon nanowire low-power ring oscillator featuring one-volt operation. Microelectronic Engineering, 2015, 145, 120-123.	2.4	5
15	Electrical Characteristics of SnO2 Thin-Film Transistors Fabricated on Bendable Substrates Using Reactive Magnetron Sputtering. Journal of Nanoscience and Nanotechnology, 2016, 16, 11697-11700.	0.9	5
16	Nanowatt power operation of silicon nanowire NAND logic gates on bendable substrates. Nano Research, 2016, 9, 3656-3662.	10.4	4
17	Low-power functionality of silicon-nanowire-assembled inverters on bendable plastics. Nano Research, 2016, 9, 1409-1417.	10.4	2
18	Si-Nanowire-Array-Based NOT-Logic Circuits Constructed on Plastic Substrates Using Top–Down Methods. Journal of Nanoscience and Nanotechnology, 2013, 13, 3350-3353.	0.9	1

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#	Article	IF	CITATIONS
19	Vertical stacking of ZnO nanowire devices with different functionalities on plastic substrates. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 1928-1932.	1.8	1
20	Field-effect modulation of the thermoelectric characteristics of silicon nanowires on plastic substrates. Nanotechnology, 2016, 27, 485401.	2.6	1
21	ZnO nanowire field-effect transistors with Pt nanocrystals fabricated on a flexible plastic substrate for a non-volatile memory application. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 1912-1916.	1.8	Ο